L Number	Hits	Search Text	DB	Time stamp
5	32	"sealant material" adj "epoxy"	USPAT;	2002/10/02 16:30
			US-PGPUB;	1002, 10, 02 10.50
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
6	0	"liquid crystal" adj "sealant material"	USPAT;	2002/10/02 16:30
		adj "epoxy"	US-PGPUB;	2002,10,02 10.30
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
7	0	"liquid crystal" adj "sealant material"	USPAT;	2002/10/02 16:31
		114000 01,0001 00, 0001000 000101	US-PGPUB;	2002, 10, 02 10.01
			EPO; JPO;	1
			DERWENT;	
			IBM TDB	
8	3	"liquid crystal" near "sealant material"	USPAT;	2002/10/02 16:31
"		riquid crystar near scarant material	US-PGPUB;	2002/10/02 10:31
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	"6330099"	USPAT;	2002/10/02 16:28
	[		US-PGPUB;	2002/10/02 10:20
			EPO; JPO;	
	ĺ		DERWENT;	
			IBM TDB	_
_	2	"6362861"	USPAT;	2002/10/02 10:29
		0302001	US-PGPUB;	2002/10/02 10:29
			EPO; JPO;	
			DERWENT;	-
			IBM TDB	
_	2231	"Agilent Technologies".AS.	USPAT;	2002/10/02 10:36
	2231	ingitions recumorogres and	US-PGPUB;	2002,10,02 10.30
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	"Agilent Technologies".AS. and 349/190	USPAT;	2002/10/02 10:37
		1.5220.00 100103205 11.01 41.4 517/170	US-PGPUB;	2332, 13, 32 13.3,
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	"anistropic etch" adj "filling hole"	USPAT;	2002/10/02 10:46
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	"anistropic etch" adj "liquid crystal	USPAT;	2002/10/02 10:47
		filling hole"	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	"anistropic etch" adj "liquid crystal"	USPAT;	2002/10/02 10:48
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	153	(349/190).CCLS.	USPAT;	2002/10/02 15:20
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	440	(438/30).CCLS.	USPAT;	2002/10/02 12:46
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	1	"anisotropic etch" adj "silicon wafer"	USPĀT;	2002/10/02 12:55
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
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-	3	"anisotropic etch" near "silicon wafer"	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/10/02 12:56
-	61	"anisotropic etching" adj "silicon wafer"	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/10/02 13:14
-	0	"anisotropic etching" near "liquid crystal"	DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/10/02 13:15
-	0	"anisotropic etching" near "liquid crystal substrate"	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/10/02 13:15
-	708	"anisotropic etching" near "substrate"	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/10/02 13:23
_	144	(349/154).CCLS.	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/10/02 13:26
_	10	"injection hole" adj "substrate"	EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/10/02 13:43
-	0	"sealant" adj "glue, epoxy, solder"	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/10/02 13:46
	0	"sealant material" adj "glue, epoxy,and	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/10/02 13:46
		solder"	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	
-	311	"sealant" adj "epoxy"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/10/02 13:54
-	3	"liquid crystal" adj "microdisplays"	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/10/02 14:22
-	83	"testing" adj "liquid crystal display"	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/10/02 14:29
_	0	"testing" adj "liquid crystal micro display"	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/10/02 14:27
_	0	"testing" adj "sealing hole"	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/10/02 14:29
			DERWENT; IBM_TDB	



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-	0	"testing" adj " liquid crystal sealing	USPAT;	2002/10/02 14:30
		hole"	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	"6330099"	USPAT;	2002/10/02 15:09
			US-PGPUB;	
ŀ			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	(349/190 and testing).CCLS.	USPĀT;	2002/10/02 15:18
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1			IBM TDB	
	0	349/190 adj testing	USPAT;	2002/10/02 15:18
			US-PGPUB;	
			EPO; JPO;	
	1		DERWENT;	
			IBM TDB	
_	0	349/190 near testing	USPAT;	2002/10/02 15:18
		, ,	US-PGPUB;	2002/10/02 14:10
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	"349/190" near "testing"	USPĀT;	2002/10/02 15:18
			US-PGPUB;	2002/10/02 13:10
			EPO; JPO;	
			DERWENT;	
			IBM TDB	-
_	0	"349/190" adj "testing"	USPAT;	2002/10/02 15:18
			US-PGPUB;	2002/10/02 13:10
			EPO; JPO;	
			DERWENT;	1
			IBM TDB	
_	475	(438/15).CCLS.	USPAT;	2002/10/02 15:21
		,	US-PGPUB;	2002, 10, 02 13.21
[			EPO; JPO;	
ļ			DERWENT;	
			IBM TDB	
_	98	(injection hole) adj (glue)	USPAT;	2002/10/02 16:19
		(a, oocton moto, aa, (grac)	US-PGPUB;	2002/10/02 10:19
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	L		T DM I DD	L

438/15 -> Ley to successful search
because Applicants methods
are drawn Crom
semiconductor technology
(testing, Jailure analysis)

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